



GaN HEMT Pulsed Power Transistor
 2.7 - 3.1 GHz, 30W Peak, 500us Pulse, 10% Duty Cycle

Production V1
 23 Aug 11

Features

- GaN depletion mode HEMT microwave transistor
- Common source configuration
- Broadband Class AB operation
- Thermally enhanced Cu/Mo/Cu package
- RoHS Compliant
- +50V Typical Operation
- MTTF of 114 years (Channel Temperature < 200°C)

Application

- Civilian and Military Pulsed Radar



Product Description

The MAGX-002731-030L00 is a gold metalized matched Gallium Nitride (GaN) on Silicon Carbide RF power transistor optimized for civilian and military radar pulsed applications between 2700 - 3100 MHz. Using state of the art wafer fabrication processes, these high performance transistors provide high gain, efficiency, bandwidth, ruggedness over a wide bandwidth for today's demanding application needs. The MAGX-002731-030L00 is constructed using a thermally enhanced Cu/Mo/Cu flanged ceramic package which provides excellent thermal performance. High breakdown voltages allow for reliable and stable operation in extreme mismatched load conditions unparalleled with older semiconductor technologies.

Typical RF Performance

| Freq (MHz) | Pin (W Peak) | Pout (W Peak) | Gain (dB) | Id-Pk (A) | Eff (%) |
|------------|--------------|---------------|-----------|-----------|---------|
| 2700 | 3 | 46 | 11.8 | 1.7 | 56 |
| 2900 | 3 | 43 | 11.6 | 1.6 | 53 |
| 3100 | 3 | 41 | 11.2 | 1.5 | 56 |

Typical RF performance measured in M/A-COM RF test fixture. Devices tested in common source Class-AB configuration as follows: V_{dd}=50V, I_{dq}=250mA (pulsed), F=2.7—3.1 GHz, Pulse=500us, Duty=10%.

Ordering Information

MAGX-002731-030L00 30W GaN Power Transistor
 MAGX-002731-SB1PPR Evaluation Fixture

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Absolute Maximum Ratings Table (1, 2, 3)

| | |
|-------------------------------------------------------------------------------------|---------------------------|
| Supply Voltage (Vdd) | +65V |
| Supply Voltage (Vgg) | -8 to 0V |
| Supply Current (Id1) | 3000 mA |
| Input Power (Pin) | +30 dBm |
| Absolute Max. Junction/Channel Temp | 200 °C |
| Continuous Power Dissipation (Pdiss) at 85 °C | 27 W |
| Pulsed Power Dissipation (Pavg) at 85 °C | 65 W |
| MTTF (T _J <200°C) | 114 years |
| Thermal Resistance, (T _{channel} = 200 °C) Pulsed 500uS, 10% Duty cycle | 1.8 °C/W |
| Operating Temp | -40 to +95C |
| Storage Temp | -65 to +150C |
| Mounting Temperature | See solder reflow profile |
| ESD Min. - Machine Model (MM) | 50 V |
| ESD Min. - Human Body Model (HBM) | >250 V |
| MSL Level | MSL1 |

(1) Operation of this device above any one of these parameters may cause permanent damage.

(2) Channel temperature directly affects a device's MTTF. Channel temperature should be kept as low as possible to maximize lifetime.

(3) For saturated performance it recommended that the sum of (3*Vdd + abs(Vgg)) <175

| Parameter | Test Conditions | Symbol | Min | Typ | Max | Units |
|--------------------------------|--------------------------------------------------------|---------------------|-----|------|-----|-------|
| DC CHARACTERISTICS | | | | | | |
| Drain-Source Leakage Current | V _{GS} = -8V, V _{DS} = 175V | I _{DS} | - | - | 2.5 | mA |
| Gate Threshold Voltage | V _{DS} = 5V, I _D = 6mA | V _{GS(th)} | -5 | -3 | -2 | V |
| Forward Transconductance | V _{DS} = 5V, I _D = 1.5mA | G _M | 1.0 | - | - | S |
| DYNAMIC CHARACTERISTICS | | | | | | |
| Input Capacitance | V _{DS} = 0v, V _{GS} = -8V, F = 1MHz | C _{ISS} | - | 13.2 | - | pF |
| Output Capacitance | V _{DS} = 50V, V _{GS} = -8V, F = 1MHz | C _{OSS} | - | 5.6 | - | pF |
| Reverse Transfer Capacitance | V _{DS} = 50V, V _{GS} = -8V, F = 1MHz | C _{RSS} | - | 0.5 | - | pF |

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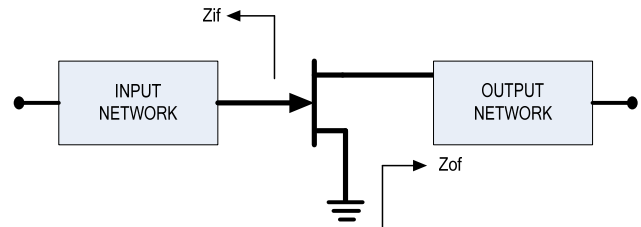
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Electrical Specifications: $T_C = 25 \pm 5^\circ\text{C}$ (Room Ambient)

| Parameter | Test Conditions | Symbol | Min | Typ | Max | Units |
|-------------------------|-----------------|-----------|---------|---------|-----|-----------------|
| Output Power | Pin = 3W Peak | P_{OUT} | 30 3 | 40 4 | - | W Peak W Ave |
| Power Gain | Pin = 3W Peak | G_P | 10 | 11.4 | - | dB |
| Drain Efficiency | Pin = 3W Peak | η_D | 50 | 55 | - | % |
| Load Mismatch Stability | Pin = 3W Peak | VSWR-S | 5:1 | - | - | - |
| Load Mismatch Tolerance | Pin = 3W Peak | VSWR-T | 10:1 | - | - | - |

Test Fixture Impedance

| F (MHz) | Z_{IF} (Ω) | Z_{OF} (Ω) |
|---------|-----------------------|-----------------------|
| 2700 | 9.2 - j10.7 | 4.21 - j0.06 |
| 2900 | 7.7 - j7.3 | 5.58 + j0.07 |
| 3100 | 8.3 - j8.4 | 4.82 - j0.8 |



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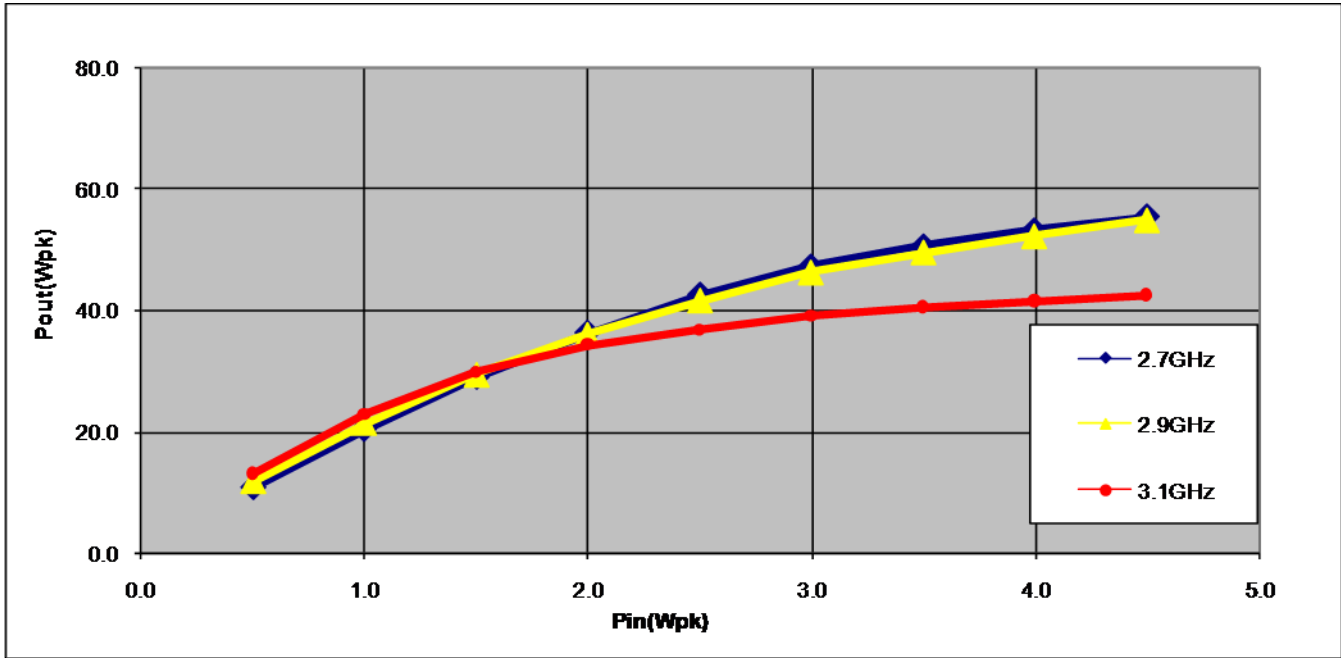
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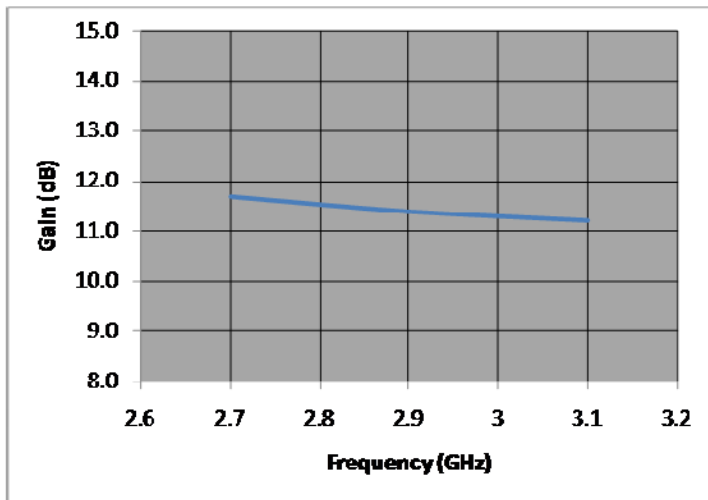
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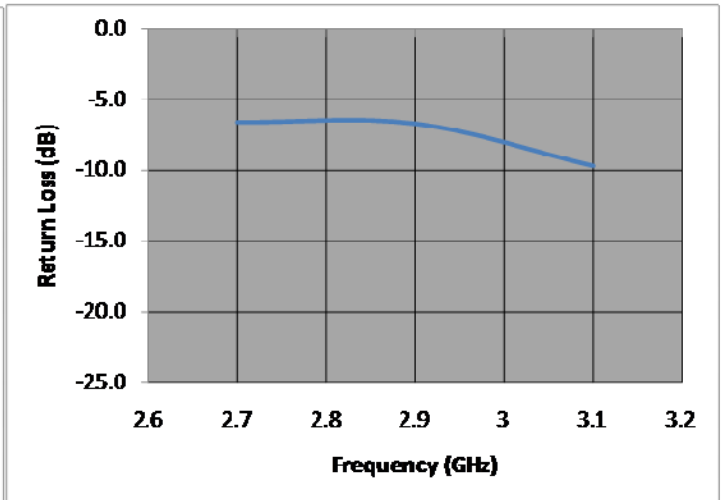
RF Power Transfer Curve at 50V Drain Bias, Idq=0.25A
Output Power vs. Input Power



Gain vs. Frequency
 50V Drain Bias, Idq=0.25A



Return Loss vs. Frequency
 50V Drain Bias, Idq=0.25A



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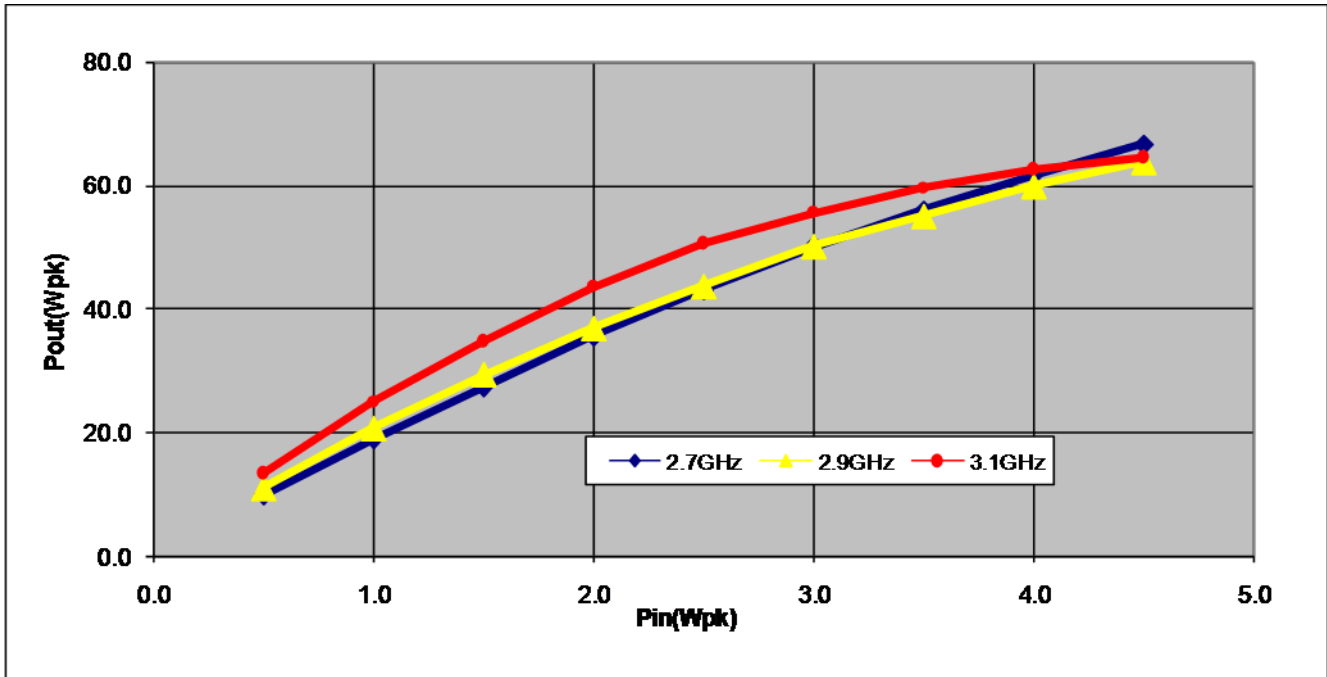
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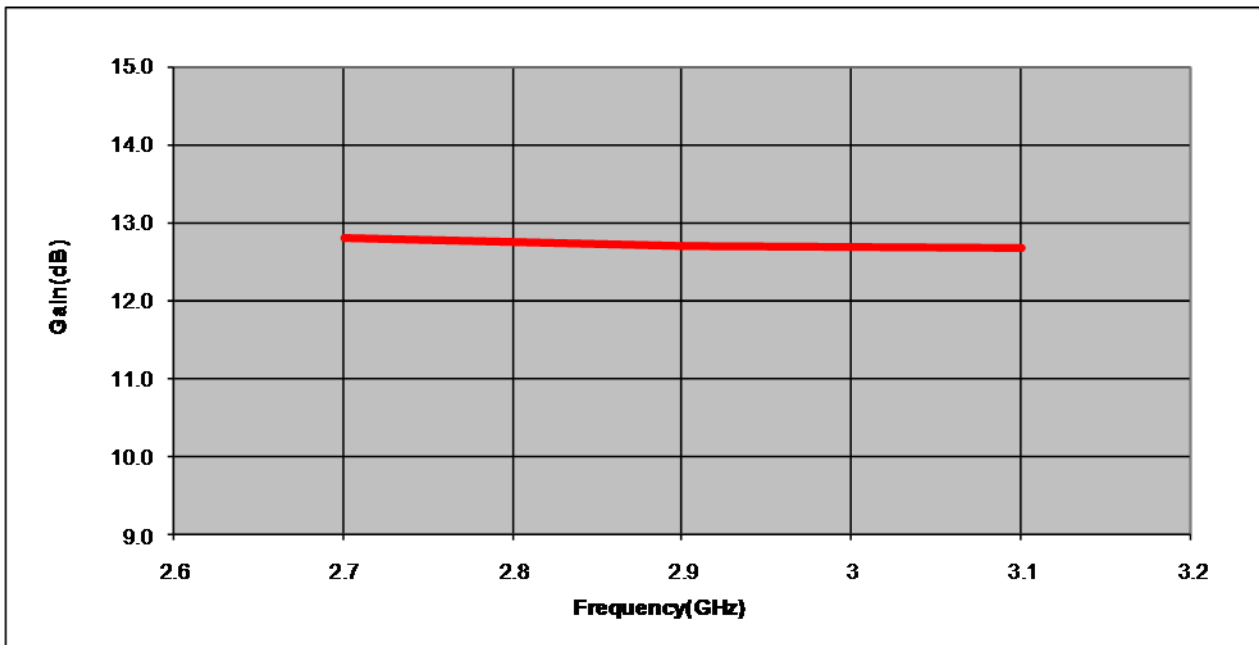
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RF Power Transfer Curve at 65V Drain Bias, Idq=0.25A
Output Power vs. Input Power



RF Power Transfer Curve at 65V Drain Bias, Idq=0.25A



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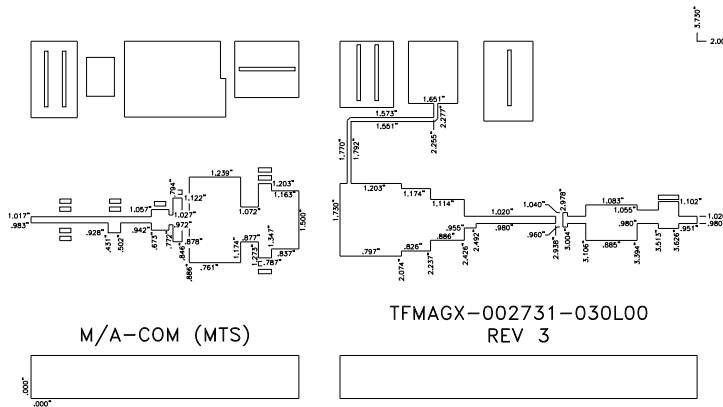
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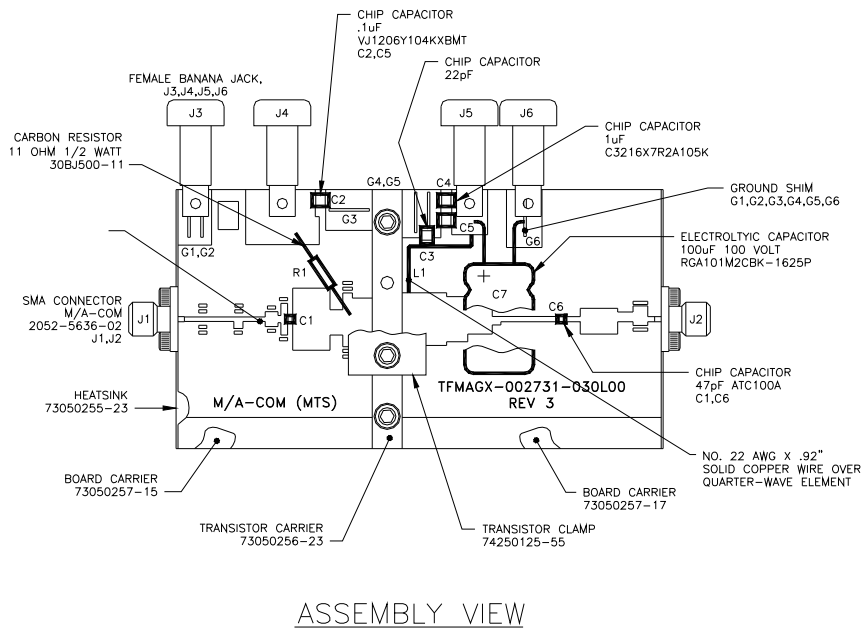
Test Fixture Circuit Dimensions

Note: A dwg circuit drawing is available upon request



CIRCUIT DIMENSIONS SCALE = 1:1

Test Fixture Assembly



ASSEMBLY VIEW

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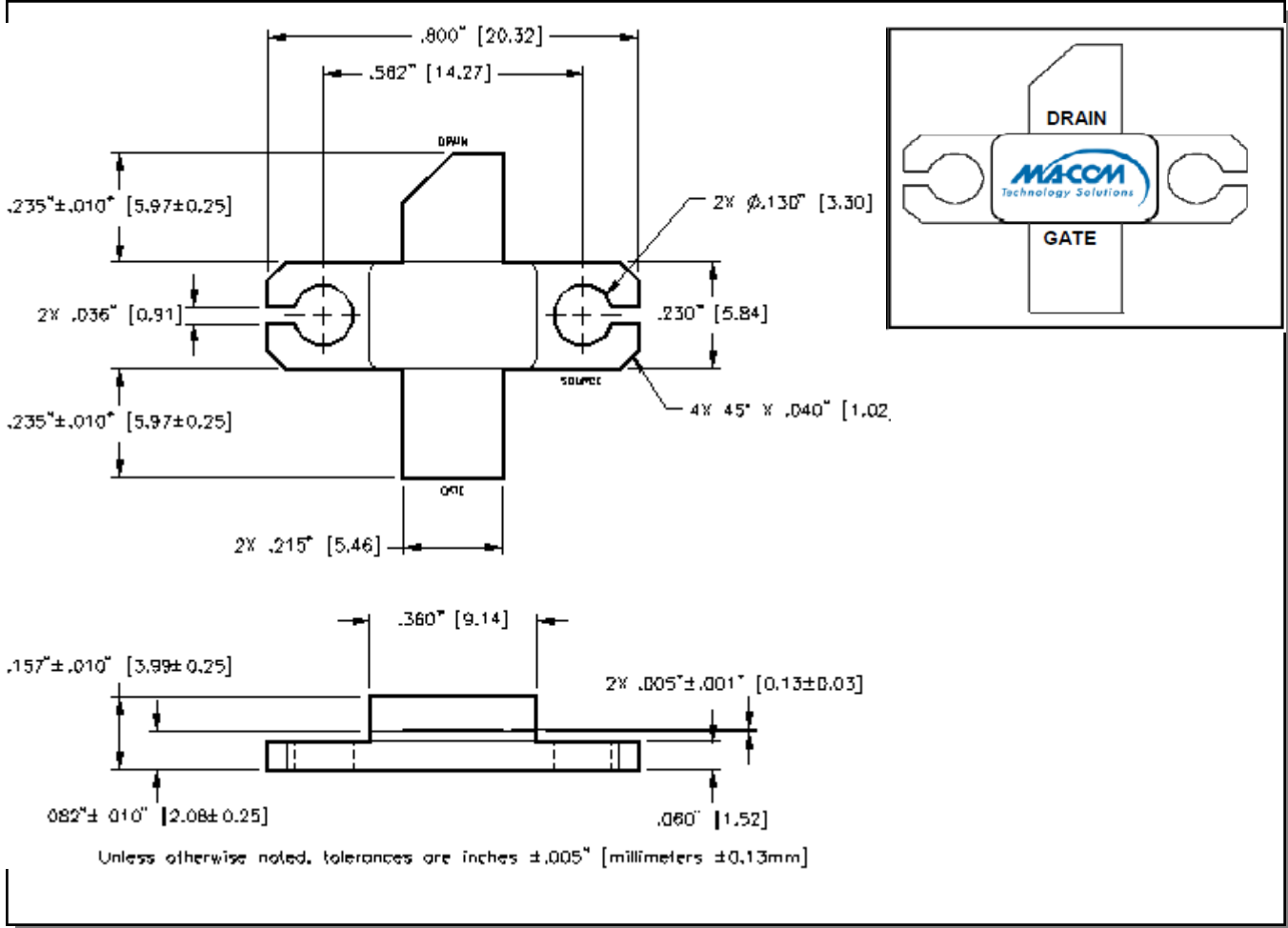
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Outline Drawings



CORRECT DEVICE SEQUENCING

TURNING THE DEVICE ON

1. Set V_{GS} to the pinch-off (V_P), typically -5V
2. Turn on V_{DS} to nominal voltage (50V)
3. Increase V_{GS} until the I_{DS} current is reached
4. Apply RF power to desired level

TURNING THE DEVICE OFF

1. Turn the RF power off
2. Decrease V_{GS} down to V_P
3. Decrease V_{DS} down to 0V
4. Turn off V_{GS}